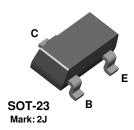


## **PN3640**

## **MMBT3640**





## **PNP Switching Transistor**

This device is designed for very high speed saturated switching at collector currents to 100 mA. Sourced from Process 65. See PN4258 for characteristics.

## **Absolute Maximum Ratings\***

TA = 25 ℃ unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	12	V
V <sub>CBO</sub>	Collector-Base Voltage	12	V
V <sub>EBO</sub>	Emitter-Base Voltage	4.0	V
I <sub>C</sub>	Collector Current - Continuous	200	mA
T <sub>J</sub> , T <sub>stg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

<sup>\*</sup>These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

- 1) These ratings are based on a maximum junction temperature of 150 degrees C.
  2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.
- 3) All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### **Thermal Characteristics** TA = 25 ℃ unless otherwise noted

Symbol	Characteristic	М	Units	
		PN3640	*MMBT3640	
$P_{D}$	Total Device Dissipation	350	225	mW
	Derate above 25°C	2.8	1.8	mW/°C
$R_{\theta JC}$	Thermal Resistance, Junction to Case	125		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	357	556	°C/W

<sup>\*</sup>Device mounted on FR-4 PCB 1.6" X 1.6" X 0.06."

# PNP Switching Transistor (continued)

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	12		V
V <sub>(BR)CES</sub>	Collector-Emitter Breakdown Voltage	$I_C = 100 \mu\text{A},  V_{BE} = 0$	12		V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	$I_C = 100 \mu\text{A}, \ I_E = 0$	12		V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	$I_E = 100  \mu A, I_C = 0$	4.0		V
I <sub>CES</sub>	Collector Cutoff Current	$V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		0.01	μА
		$V_{CE} = 6.0 \text{ V}, V_{BE} = 0, T_A = 65^{\circ}\text{C}$ $V_{CE} = 6.0 \text{ V}, V_{BE} = 0$		1.0	μA
l <sub>B</sub>	Base Current	$V_{CE} = 6.0 \ V, V_{BE} = 0$		10	nA
ON CHAR	ACTERISTICS*  DC Current Gain	$I_{C} = 10 \text{ mA}, V_{CE} = 0.3 \text{ V}$	30	120	
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	$\begin{split} &I_C = 50 \text{ mA, } V_{CE} = 1.0 \text{ V} \\ &I_C = 10 \text{ mA, } I_B = 0.5 \text{ mA} \\ &I_C = 10 \text{ mA, } I_B = 1.0 \text{ mA} \\ &I_C = 50 \text{ mA, } I_B = 5.0 \text{ mA} \\ &I_{C} = 10 \text{ mA, } I_{B} = 1.0 \text{ mA, } I_{A} = 65^{\circ}\text{C} \end{split}$	20	0.3 0.2 0.6 0.25	V V V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	$I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 0.5 \text{ mA}$ $I_C = 10 \text{ mA}, I_B = 1.0 \text{ mA}$	0.75 0.8	0.95 1.0	V
		$I_{\rm C} = 50$ mA, $I_{\rm B} = 5.0$ mA		1.5	V
	GNAL CHARACTERISTICS		500	1.5	
	GNAL CHARACTERISTICS  Current Gain - Bandwidth Product	$I_{C} = 50 \text{ mA}, I_{B} = 5.0 \text{ mA}$ $I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 100 \text{ MHz}$	500	1.5	V MHz
т		$I_{C} = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$	500	3.5	•
F <sub>T</sub>	Current Gain - Bandwidth Product	$I_{C}$ = 10 mA, $V_{CE}$ = 5.0 V, $f$ = 100 MHz $V_{CB}$ = 5.0 V, $I_{E}$ = 0,	500		MHz
C <sub>ibo</sub>	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 5.0 \ V, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \ V, \ I_{E} = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \ V, \ I_{C} = 0, \\ f &= 1.0 \text{ MHz} \end{split}$	500	3.5	MHz pF
T Cobo Cibo SWITCHIN	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time	$\begin{split} I_{C} &= 10 \text{ mA, } V_{CE} = 5.0 \text{ V,} \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V, } I_{E} = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \text{ V, } I_{C} = 0, \end{split}$	500	3.5	MHz pF
C <sub>obo</sub> C <sub>ibo</sub> SWITCHIN	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time	$\begin{split} I_{C} &= 10 \text{ mA}, \ V_{CE} = 5.0 \ \text{V}, \\ f &= 100 \ \text{MHz} \\ V_{CB} &= 5.0 \ \text{V}, \ I_{E} = 0, \\ f &= 1.0 \ \text{MHz} \\ V_{BE} &= 0.5 \ \text{V}, \ I_{C} = 0, \\ f &= 1.0 \ \text{MHz} \\ \end{split}$	500	3.5	MHz pF pF
Cobo  Cibo  SWITCHIN	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time Storage Time	$\begin{split} I_C &= 10 \text{ mA}, \ V_{CE} = 5.0 \ \text{V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \ \text{V}, \ I_E = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $V_{BE} &= 0.5 \ \text{V}, \ I_C = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $V_{CC} &= 6.0 \ \text{V}, \ V_{BE(off)} = 1.9 \ \text{V}, \\ I_C &= 50 \ \text{mA}, \ I_{B1} = 5.0 \ \text{mA}, \\ V_{CC} &= 6.0 \ \text{V}, \ I_C = 50 \ \text{mA}, \end{split}$	500	3.5 3.5 10 30 20	MHz pF pF
T Cobo Cibo SWITCHING Id Ir	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time	$\begin{split} I_C &= 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $V_{CC} = 6.0 \text{ V}, \ V_{BE(off)} = 1.9 \text{ V}, \\ I_C &= 50 \text{ mA}, \ I_{B1} = 5.0 \text{ mA} \\ V_{CC} &= 6.0 \text{ V}, \ I_C = 50 \text{ mA}, \\ I_{B1} &= I_{B2} = 5.0 \text{ mA} \end{split}$	500	3.5 3.5 10 30	MHz pF pF ns
Cobo  Cibo  SWITCHIN  td  tr	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time Storage Time	$\begin{split} I_C &= 10 \text{ mA},  V_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V},  I_E = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \text{ V},  I_C = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $\begin{aligned} V_{CC} &= 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \\ I_C &= 50 \text{ mA},  I_{B1} = 5.0 \text{ mA} \\ V_{CC} &= 6.0 \text{ V},  I_C = 50 \text{ mA}, \\ I_{B1} &= I_{B2} = 5.0 \text{ mA} \\ \end{aligned}$ $\begin{aligned} V_{CC} &= 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \\ I_C &= 50 \text{ mA},  I_{B1} = 5.0 \text{ mA} \end{aligned}$	500	3.5 3.5 10 30 20	MHz pF pF ns ns
T Cobo Cibo  SWITCHING or s	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{split} I_C &= 10 \text{ mA}, \ V_{CE} = 5.0 \text{ V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \text{ V}, \ I_E = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \text{ V}, \ I_C = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $\begin{split} V_{CC} &= 6.0 \text{ V}, \ V_{BE(off)} = 1.9 \text{ V}, \\ I_C &= 50 \text{ mA}, \ I_{B1} = 5.0 \text{ mA} \\ V_{CC} &= 6.0 \text{ V}, \ I_C = 50 \text{ mA}, \\ I_{B1} &= I_{B2} = 5.0 \text{ mA} \\ \end{split}$ $V_{CC} &= 6.0 \text{ V}, \ V_{BE(off)} = 1.9 \text{ V}, \\ \end{split}$	500	3.5 3.5 10 30 20 12	MHz pF pF ns ns ns
Cobo  Cibo  SWITCHIN  td  tr  ts  tf	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time	$\begin{split} I_C &= 10 \text{ mA}, \ V_{CE} = 5.0 \ \text{V}, \\ f &= 100 \text{ MHz} \\ V_{CB} &= 5.0 \ \text{V}, \ I_E = 0, \\ f &= 1.0 \text{ MHz} \\ V_{BE} &= 0.5 \ \text{V}, \ I_C = 0, \\ f &= 1.0 \text{ MHz} \\ \end{split}$ $\begin{aligned} V_{CC} &= 6.0 \ \text{V}, \ V_{BE(off)} = 1.9 \ \text{V}, \\ I_C &= 50 \ \text{mA}, \ I_{B1} = 5.0 \ \text{mA} \\ V_{CC} &= 6.0 \ \text{V}, \ I_C = 50 \ \text{mA}, \\ I_{B1} &= I_{B2} = 5.0 \ \text{mA} \\ V_{CC} &= 6.0 \ \text{V}, \ V_{BE(off)} = 1.9 \ \text{V}, \\ I_C &= 50 \ \text{mA}, \ I_{B1} = 5.0 \ \text{mA} \\ V_{CC} &= 1.5 \ \text{V}, \ I_C = 10 \ \text{mA}, \end{aligned}$	500	3.5 3.5 10 30 20 12 25	MHz pF pF ns ns ns ns
C <sub>obo</sub>	Current Gain - Bandwidth Product Output Capacitance Input Capacitance  NG CHARACTERISTICS Delay Time Rise Time Storage Time Fall Time Turn-On Time	$\begin{split} &I_C = 10 \text{ mA},  V_{CE} = 5.0 \text{ V}, \\ &f = 100 \text{ MHz} \\ &V_{CB} = 5.0 \text{ V},  I_E = 0, \\ &f = 1.0 \text{ MHz} \\ &V_{BE} = 0.5 \text{ V},  I_C = 0, \\ &f = 1.0 \text{ MHz} \\ \end{split}$ $\begin{aligned} &V_{CC} = 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \\ &I_C = 50 \text{ mA},  I_{B1} = 5.0 \text{ mA} \\ &V_{CC} = 6.0 \text{ V},  I_C = 50 \text{ mA}, \\ &I_{B1} = I_{B2} = 5.0 \text{ mA} \\ \end{aligned}$ $\begin{aligned} &V_{CC} = 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \\ &I_C = 50 \text{ mA},  I_{B1} = 5.0 \text{ mA} \\ \end{aligned}$ $\begin{aligned} &V_{CC} = 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \\ &I_C = 50 \text{ mA},  I_{B1} = 5.0 \text{ mA} \\ \end{aligned}$ $\begin{aligned} &V_{CC} = 1.5 \text{ V},  I_C = 10 \text{ mA}, \\ &I_{B1} = I_{B2} = 0.5 \text{ mA} \\ \end{aligned}$ $\begin{aligned} &V_{CC} = 6.0 \text{ V},  V_{BE(off)} = 1.9 \text{ V}, \end{aligned}$	500	3.5 3.5 10 30 20 12 25 60	MHz pF pF ns ns ns ns

<sup>\*</sup>Pulse Test: Pulse Width  $\leq$  300  $\mu$ s, Duty Cycle  $\leq$  2.0%

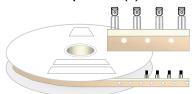
**NOTE:** All voltages (V) and currents (A) are negative polarity for PNP transistors.

#### **TO-92 Tape and Reel Data** FAIRCHILD SEMICONDUCTOR TM **TO-92 Packaging** Configuration: Figure 1.0 **TAPE and REEL OPTION** FSCINT Label sample See Fig 2.0 for various Reeling Styles CBVK//418019 **FSCINT** Label 5 Reels per Intermediate Box Customized F63TNR Label sample Label F63TNR LOT: CBVK741B019 QTY: 2000 FSID: PN222N Customized QTY1: QTY2: 375mm x 267mm x 375mm Intermediate Box TO-92 TNR/AMMO PACKING INFROMATION **AMMO PACK OPTION** See Fig 3.0 for 2 Ammo Packing Style Quantity EOL code **Pack Options** 2,000 D26Z Е 2,000 D27Z Ammo М 2,000 D74Z 2,000 D75Z **FSCINT** Unit weight = 0.22 gm Reel weight with components = 1.04 kg Ammo weight with components = 1.02 kg Max quantity per intermediate box = 10,000 units Label 5 Ammo boxes per Intermediate Box 327mm x 158mm x 135mm Immediate Box Customized F63TNR Customized Label Label 333mm x 231mm x 183mm Intermediate Box (TO-92) BULK PACKING INFORMATION **BULK OPTION** See Bulk Packing DESCRIPTION QUANTITY Information table J18Z TO-18 OPTION STD 2.0 K / BOX Anti-static Bubble Sheets TO-5 OPTION STD NO LEAD CLIP 1.5 K / BOX J05Z **FSCINT Label** NO EOL TO-92 STANDARD STRAIGHT FOR: PKG 92, NO LEADCLIP 2.0 K / BOX 94 (NON PROELECTRON SERIES), 96 TO-92 STANDARD STRAIGHT FOR: PKG 94 (PROELECTRON SERIES BCXXX, BFXXX, BSRXXX), 97, 98 L34Z NO LEADCLIP 2.0 K / BOX 2000 units per 114mm x 102mm x 51mm EO70 box for std option Immediate Box 5 EO70 boxes per intermediate Box 530mm x 130mm x 83mm Customized Intermediate box Label FSCINT Label 10,000 units maximum per intermediate box for std option

## TO-92 Tape and Reel Data, continued

# **TO-92 Reeling Style Configuration:** Figure 2.0

## Machine Option "A" (H)

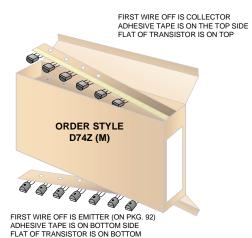


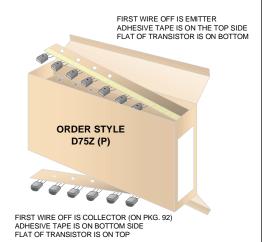
Style "A", D26Z, D70Z (s/h)

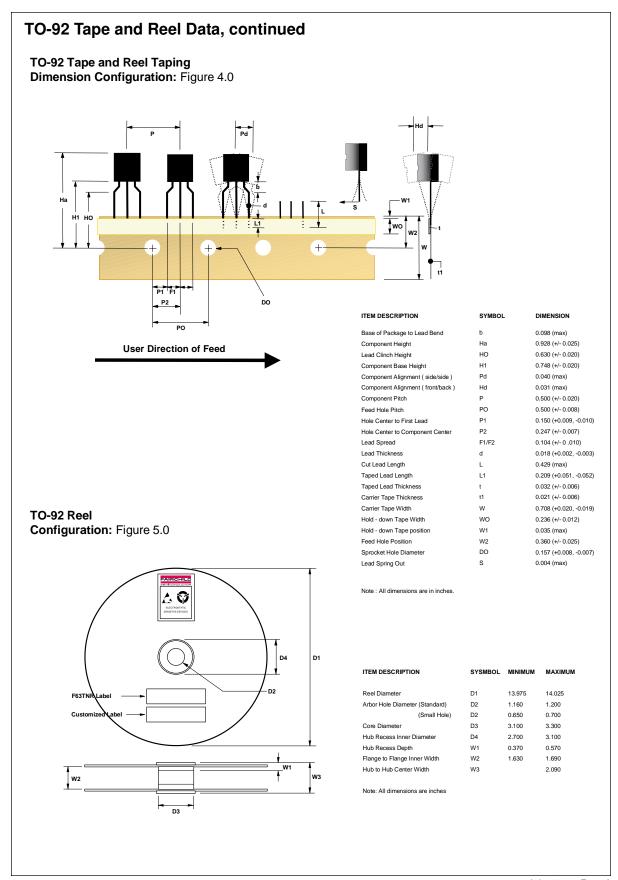
# Machine Option "E" (J)

Style "E", D27Z, D71Z (s/h)

# **TO-92 Radial Ammo Packaging Configuration:** Figure 3.0



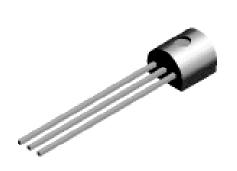


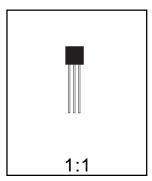


## **TO-92 Package Dimensions**



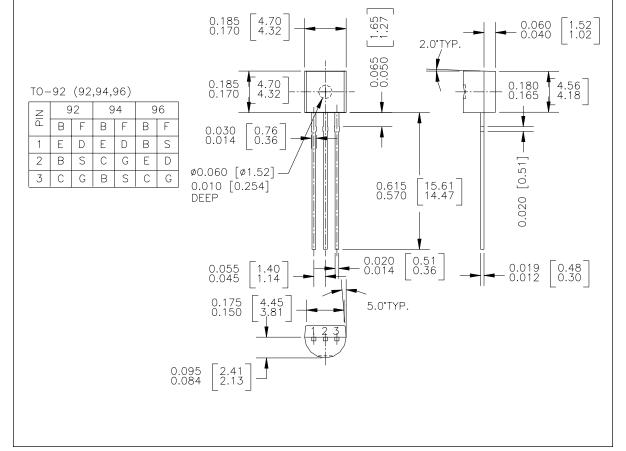
# TO-92 (FS PKG Code 92, 94, 96)

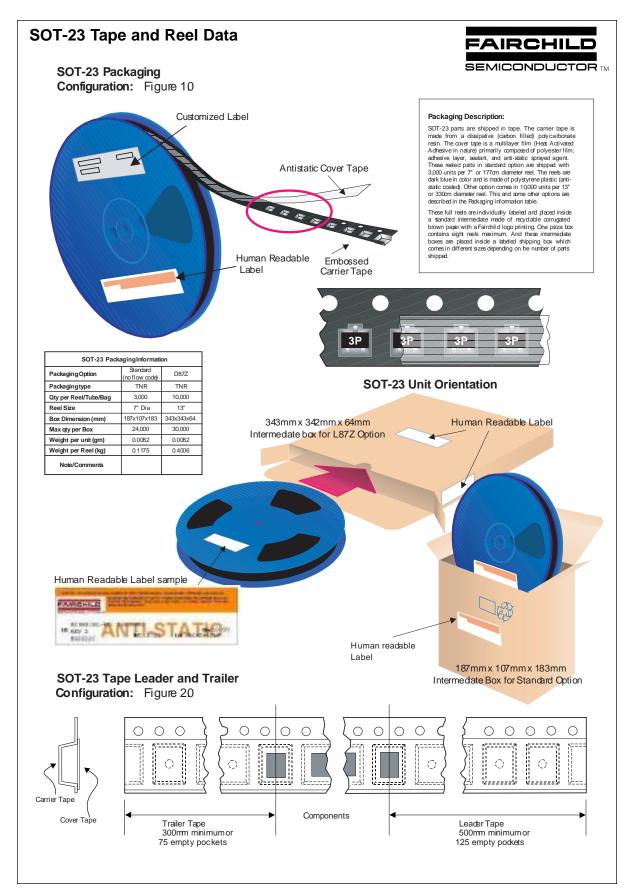




Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

Part Weight per unit (gram): 0.1977

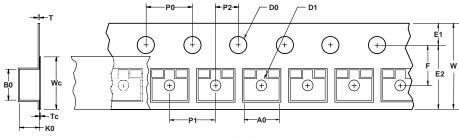




## SOT-23 Tape and Reel Data, continued

## **SOT-23 Embossed Carrier Tape**

Configuration: Figure 3.0



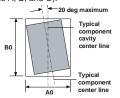
User Direction of Feed

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
<b>SOT-23</b> (8mm)	3.15 +/-0.10	2.77 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.30 +/-0.10	0.228 +/-0.013	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

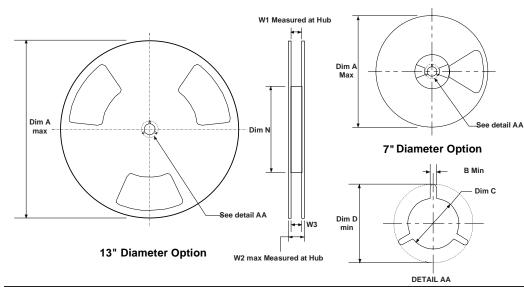


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

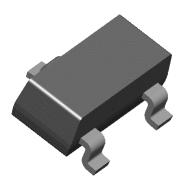
## SOT-23 Reel Configuration: Figure 4.0

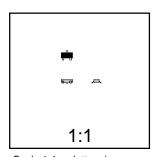


	Dimensions are in inches and millimeters								
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9



# SOT-23 (FS PKG Code 49)

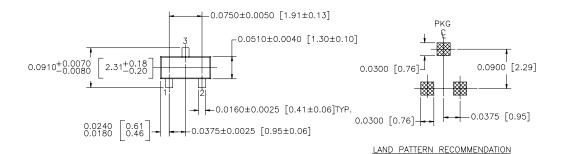


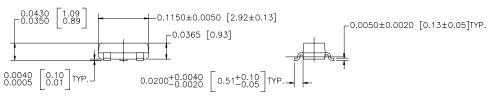


Scale 1:1 on letter size paper

Dimensions shown below are in: inches [millimeters]

Part Weight per unit (gram): 0.0082





CONTROLLING DIMENSION IS INCH VALUES IN [ ] ARE MILLIMETERS SOT 23, 3 LEADS LOW PROFILE

NOTE: UNLESS OTHERWISE SPECIFIED

- 1. STANDARD LEAD FINISH 150 MICROINCHES / 3.81 MICROMETERS MINIMUM TIN / LEAD (SOLDER) ON ALLOY 42
- 2. REFERENCE JEDEC REGISTRATION TO-236, VARIATION AB, ISSUE G, DATED JUL 1993

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DOME™ ISOPLANAR™ Quiet Series™

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- 2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

### PRODUCT STATUS DEFINITIONS

#### **Definition of Terms**

Datasheet Identification	Product Status	Definition				
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.				
Preliminary	First Production	This datasheet contains preliminary data, and supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.				
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild semiconductor. The datasheet is printed for reference information only.				